TOSHIBA Field Effect Transistor with Built-in Schottky Barrier Diode Silicon N-Channel MOS Type (U-MOS V-H)

TPC8A03-H

High Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Built-in schottky barrier diode
 Low forward voltage: V_{DSF} = -0.6 V (max)
- · High-speed switching
- Small gate charge: Q_{SW} = 8.4 nC (typ.)
- Low drain-source ON-resistance: $R_{DS (ON)} = 4.1 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance: |Yfs| = 54 S (typ.)
- Low leakage current: I_{DSS} = 100 μA (max) (V_{DS} = 30 V)
- Enhancement mode: V_{th} = 1.3 to 2.3 V (V_{DS} = 10 V, I_D = 1 mA).

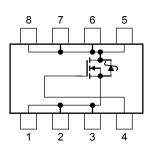
Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	30	y	
Drain-gate voltage (R _{GS} = 20 kΩ)		V _{DGR}	30	< <u>v</u>	
Gate-source voltage		V _{GS} S	±20	V	
Drain aurrant	DC (Note 1)	P	<u>/</u> 17	\ A	
Drain current	Pulsed (Note 1)	((I _{DP}))	68	\\ \^	
Drain power dissipation (t = 10 s) (Note 2a)		PD	1.9	W	
Drain power dissipation (t = 10 s) (Note 2b)		PD	(1.0/5)	W	
Single-pulse avalanche energy (Note 3)		EAS	188	mJ	
Avalanche current		I _{AR}	17	Α	
Repetitive avalanche energy (Tc = 25°C) (Note 4)		EAR	0.108	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	
Storage temperature	range	retg	-55 (0 150	.0	

Note: For Notes 1 to 4, refer to the next page.

Weight: 0.085g (typ.)

Circuit Configuration



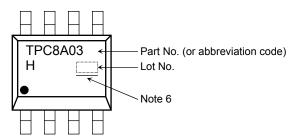
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.)

This transistor is an electrostatic-sensitive device. Handle with care.

Thermal Characteristics

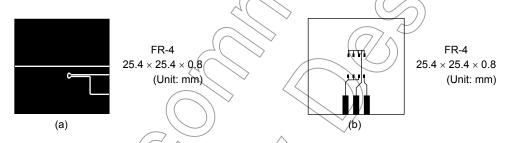
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R _{th (ch-a)}	65.8	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2b)	R _{th (ch-a)}	125	°C/W

Marking (Note 5)



Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: (a) Device mounted on a glass-epoxy board (b) Device mounted on a glass-epoxy board (b)



Note 3: $V_{DD} = 24 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), L = 0.5 mH, $R_G = 25 \Omega$, $L_{AR} = 17 \text{ A}$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5:

* Weekly code: (Three digits)

Week of manufacture
(01 for first week of year, continuing up to 52 or 53)

Year of manufacture

(The last digit of the calendar year)

Note 6: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

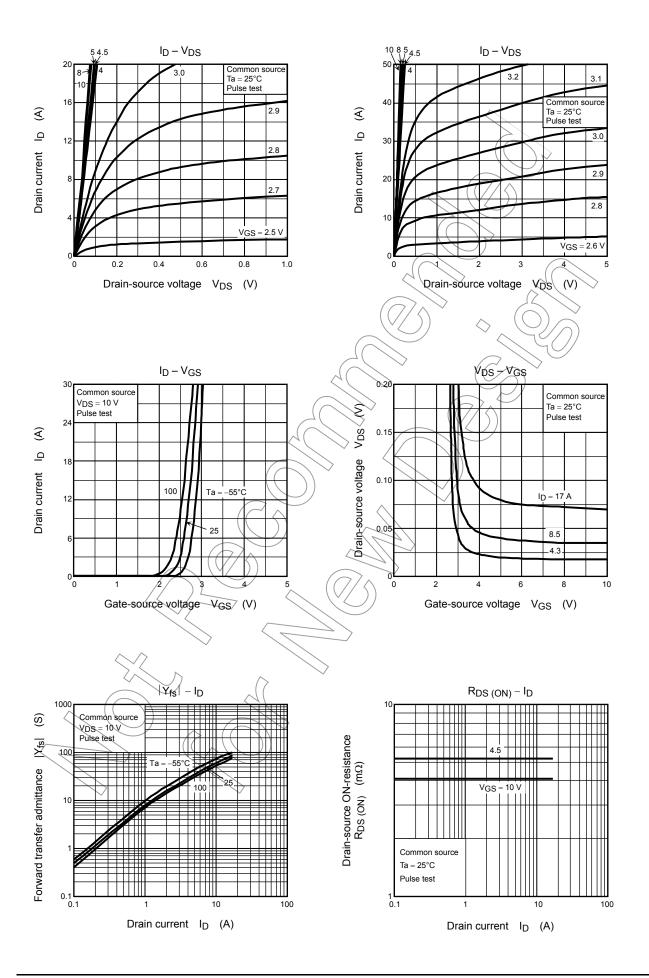
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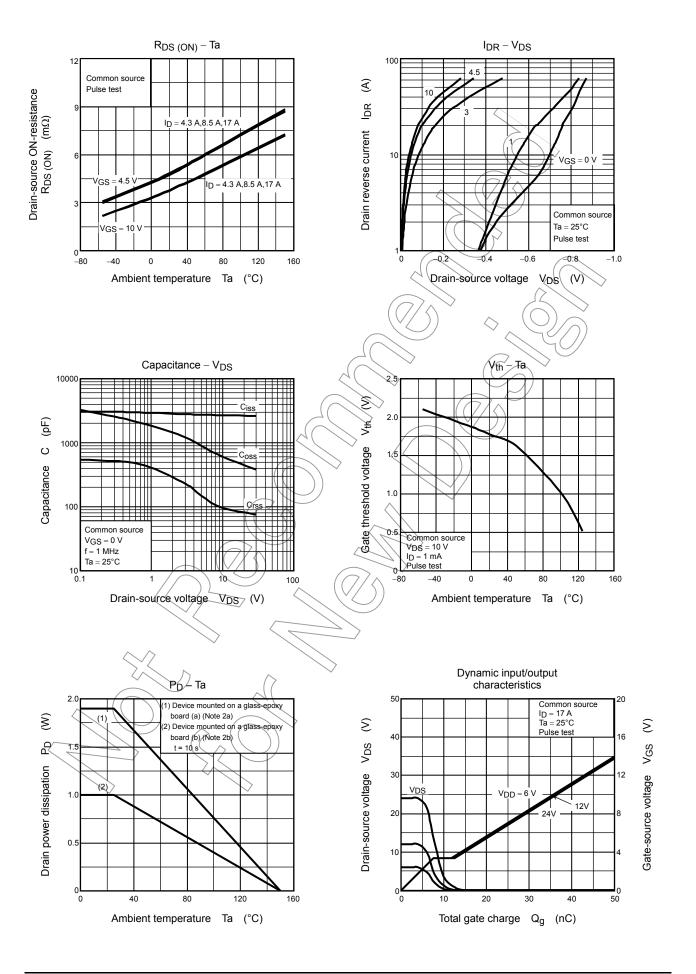
Electrical Characteristics (Ta = 25°C)

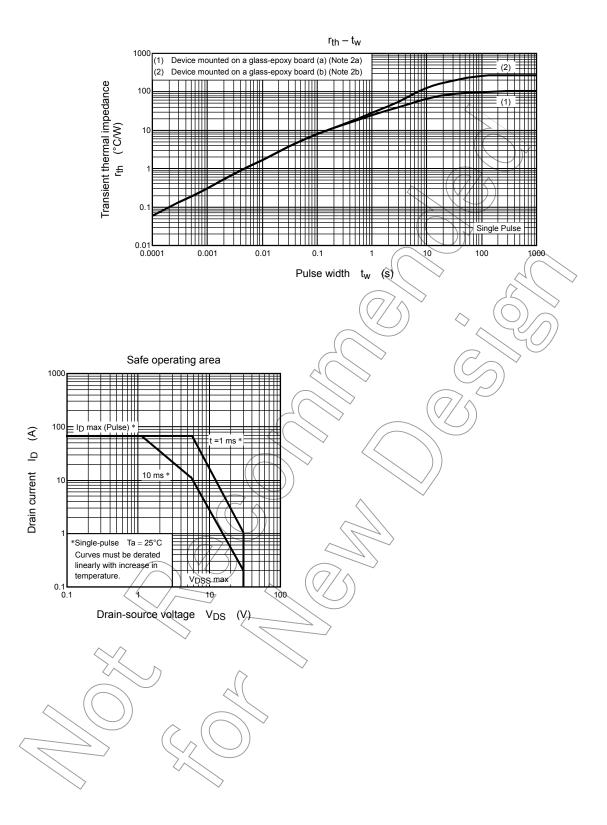
Cha	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage curr	rent	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA	
Drain cut-off curre	ent	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	_	_	100	μА	
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	V	
		V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	_	_		
Gate threshold vo	ltage	V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	1.3) >	2.3	٧	
Drain-source ON-	Drain course ON resistance		V _{GS} = 4.5 V, I _D = 8.5 A		5.1	7.0	· mΩ	
Drain-source ON-resistance		R _{DS} (ON)	V _{GS} = 10 V, I _D = 8.5 A	$\bigcirc \rangle$	4.1	5.6		
Forward transfer a	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 8.5 A	27	54	_	S	
Input capacitance		C _{iss}		<i>_</i>	2640	3430		
Reverse transfer capacitance		C _{rss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	100	150	pF	
Output capacitano	ce	Coss			610	\rightarrow		
Gate resistance		rg	V _{DS} = 10 V, V _{GS} = 0 V, f = 5 MHz	-	1.0) 1.5	Ω	
Switching time	Rise time	t _r	V _{GS} 0 V I _D = 8.5 A G _G G _G	4	3.6) _	ns	
	Turn-on time	t _{on}		\ \(\int\)	11.0			
	Fall time	t _f	4.4 W 98 T		7.2			
	Turn-off time	t _{off}	Duty ≤ 1%, t _W = 10 μs	_	42			
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 17 \text{ A}$	_	36	_		
			$V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, V_{D} \neq 17 \text{ A}$	_	19	_		
Gate-source char	ge 1 (Q _{gs1}			7.6	_	nC	
Gate-drain ("Miller") charge		Q _{gd}	$V_{DD} \approx 24 \text{ V, V}_{GS} = 10 \text{ V, I}_{D} = 17 \text{ A}$		5.0	_		
Gate switch charge		Q _{SW}			8.4	_		

Source-Drain Ratings and Characteristics (Ta = 25°C)

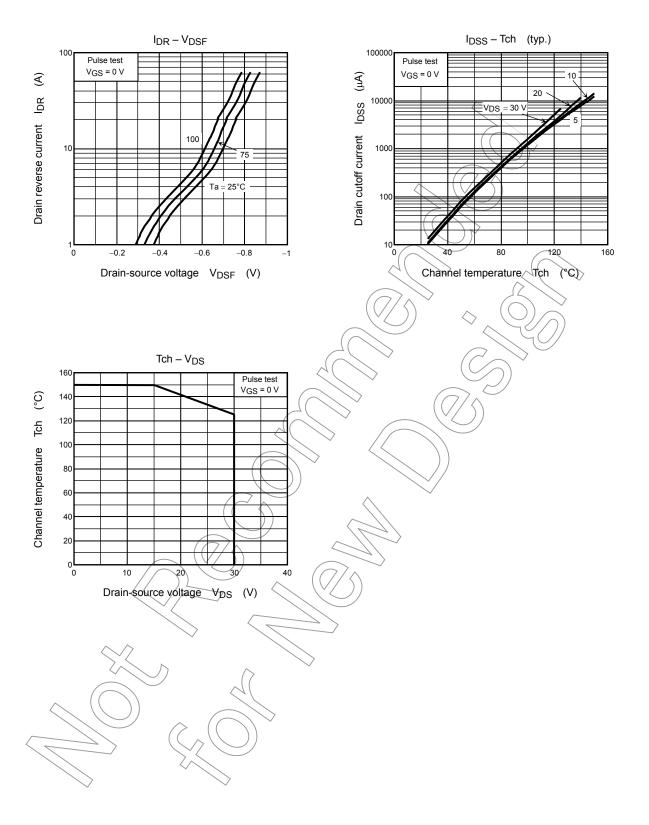
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note 1)	I _{DRP}	> -	_	_	68	Α
Equard voltage (Finds)		I _{DR} = 1 A, V _{GS} = 0 V	_	- 0.4	- 0.6	V
Forward voltage (diode)	VDSF	$I_{DR} = 17 A$, $V_{GS} = 0 V$	_	_	- 1.2	V







6 2010-01-19



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